

Indentation-induced delamination and adhesion work evaluation at elevated temperature in industrial semiconductors

Speaker: PJ Wei

24 April, 2023

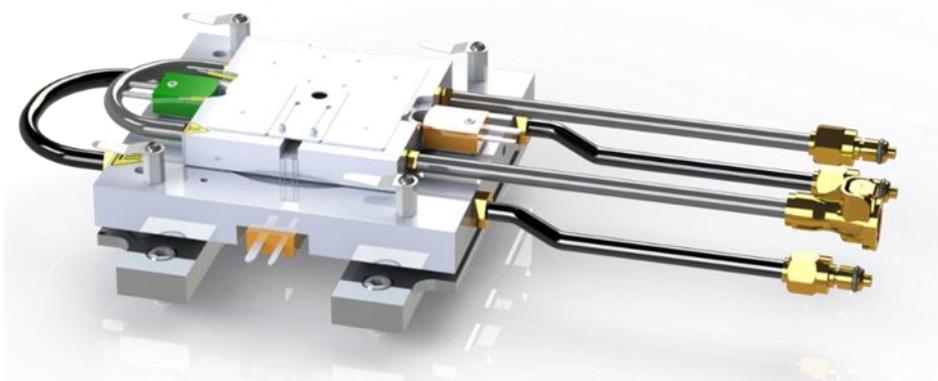
Outlines

- Basic Mechanisms of Adhesion Measurements and Correlation between Results Collected by Different Techniques
 - Applications of thin film adhesion measurement at Elevated Temperature
-

Basic Mechanisms and Methodology Correlation

Interface Bonding Issues of Adhesion in Thin Film Industries

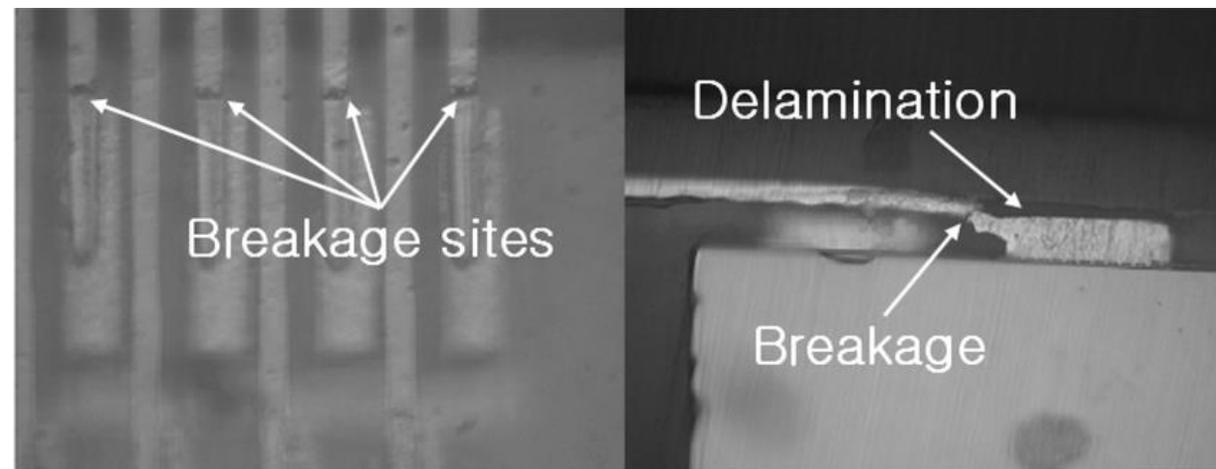
xSol® - Heating, Cooling, Humidity
Heating: 800°C • Cooling: -120°C • Humidity: 10-75% RH



<https://www.researchgate.net>

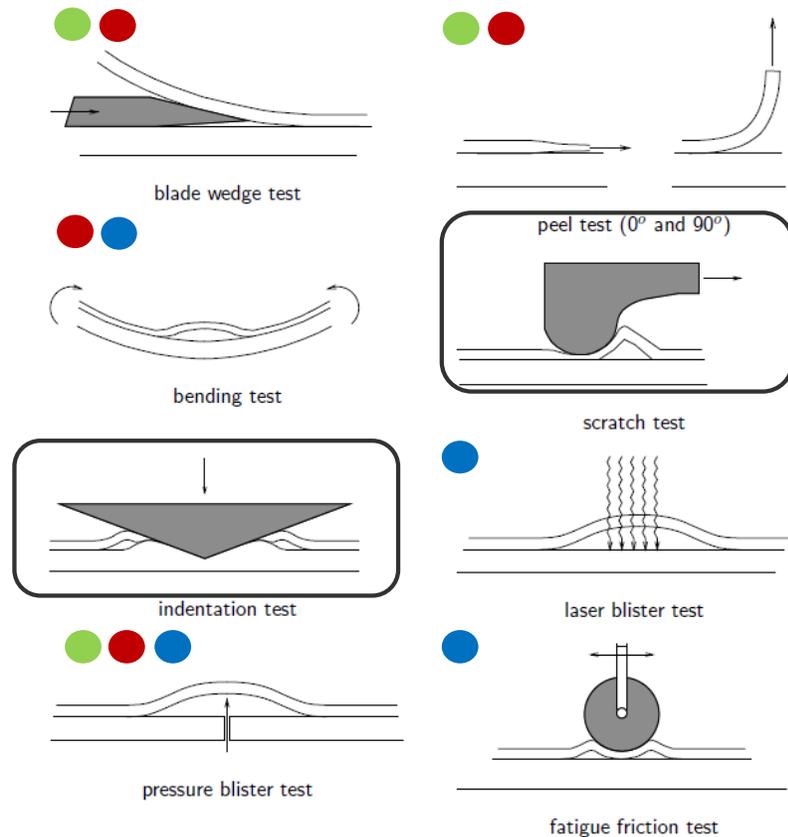


<https://outdoorsmagic.com/article/toughest-outdoor-watches-2022/>



Overview of Adhesion Metrology Techniques Measurements for Interfacial Bonding

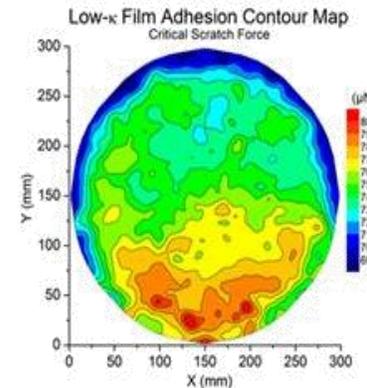
- special sample preparation
- Low spatial resolution
- Ex-situ measurement



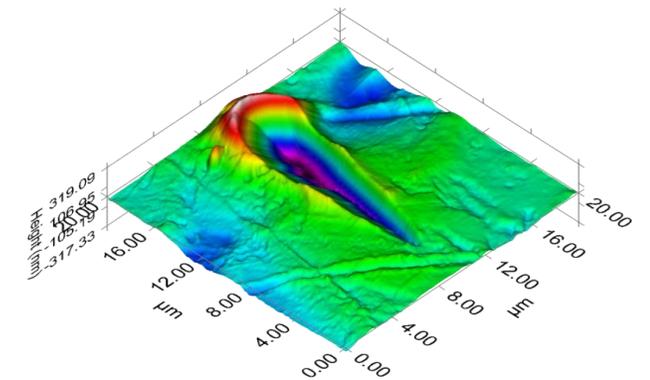
Methods to measure thin film adhesion

Nano indenter's Advantages:

1. Direct measurements
Nanoindentation or nanoscratch tests can directly performed on product surface.
No sample preparations are needed.
2. High spatial resolution
Nanoindentations or nanoscratches are at sub-micron or micron scale.

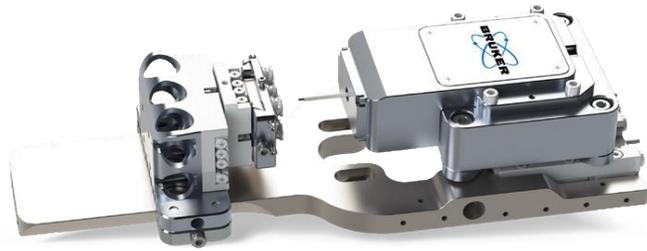


12" Wafer Adhesion Mapping



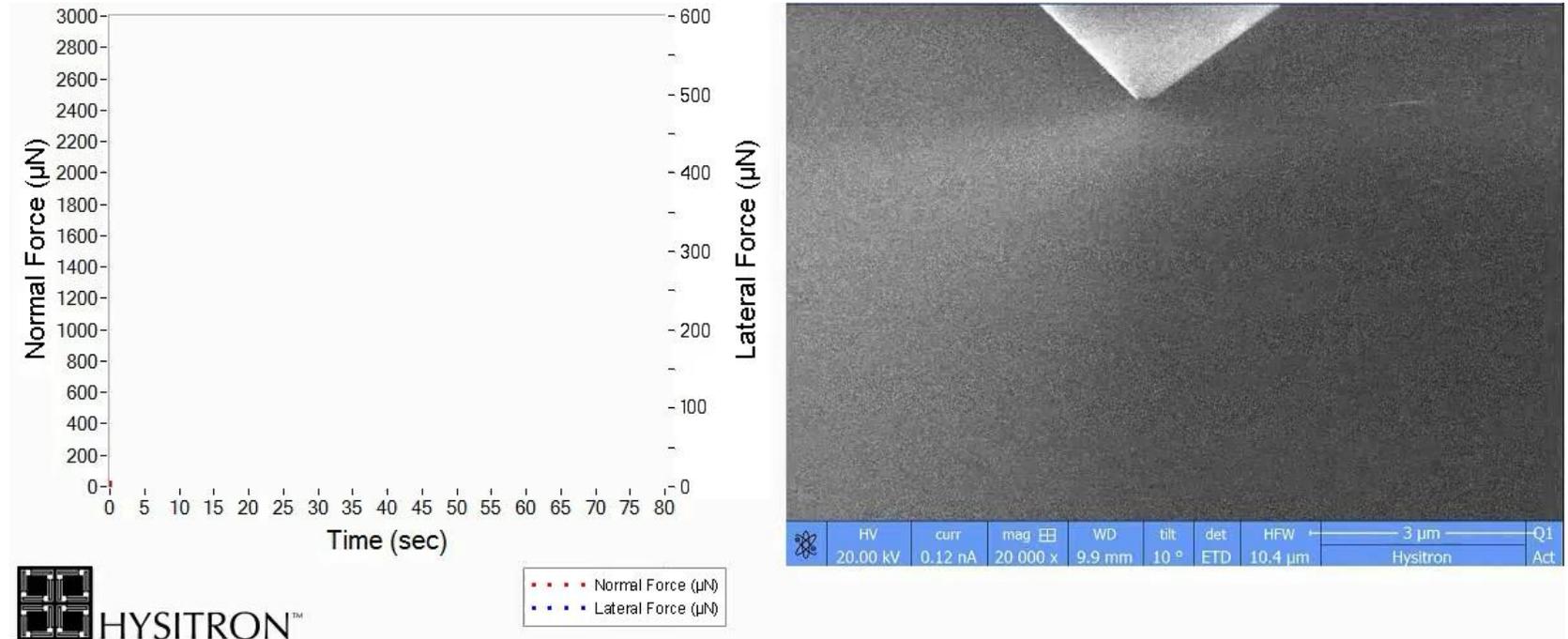
SPM of Nano scratch

Scratch-Induced Cohesion and Adhesion on Low-k Film

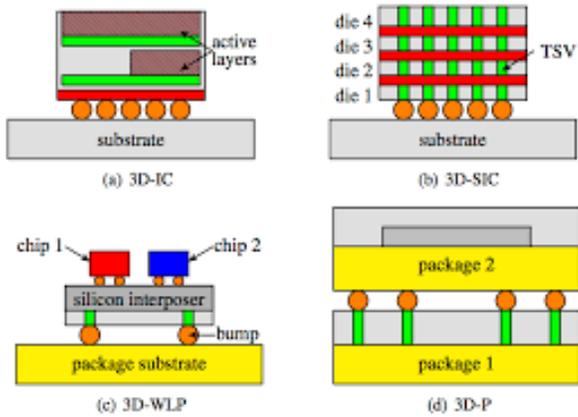


Hysitron PI 89 Picoindenter

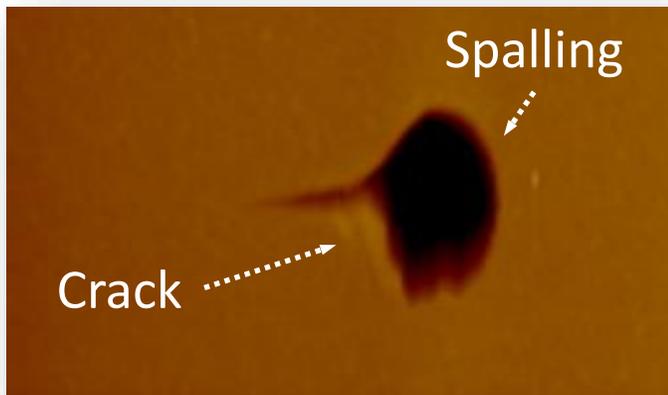
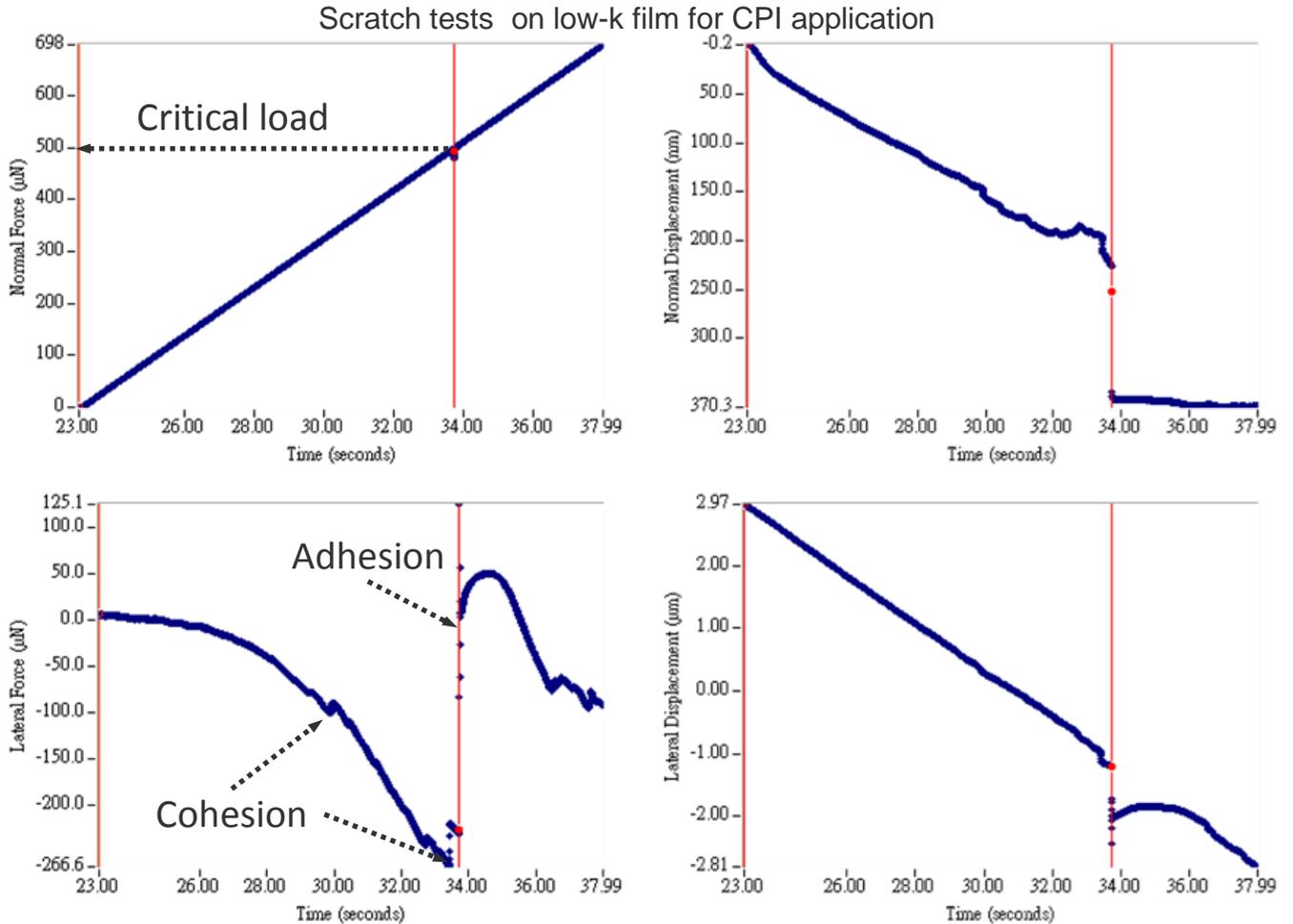
In-situ Nano-Scratch in SEM



Scratch-Induced Cohesion and Adhesion of Low-k Film

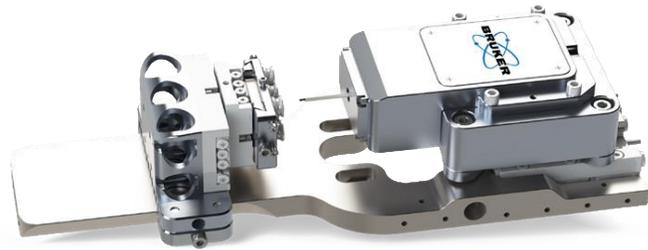


<https://www.iue.tuwien.ac.at>

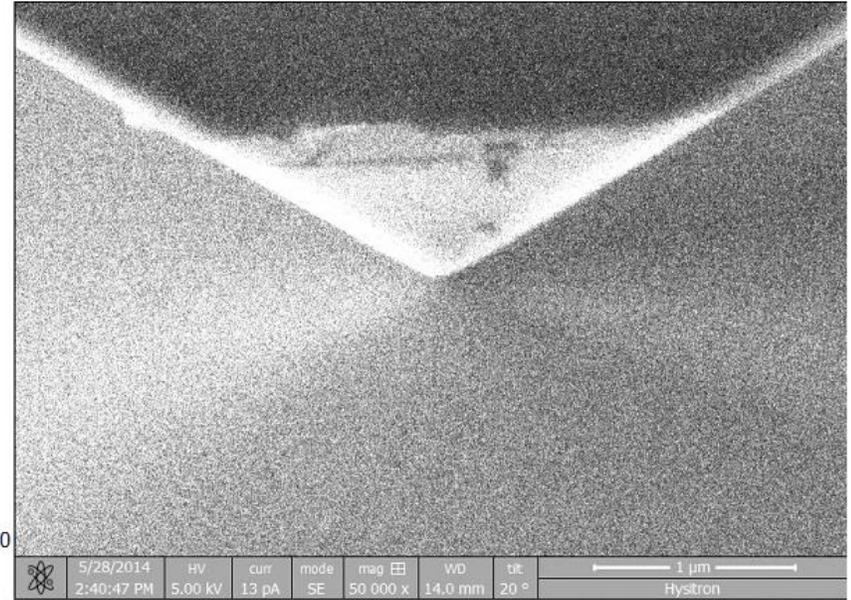
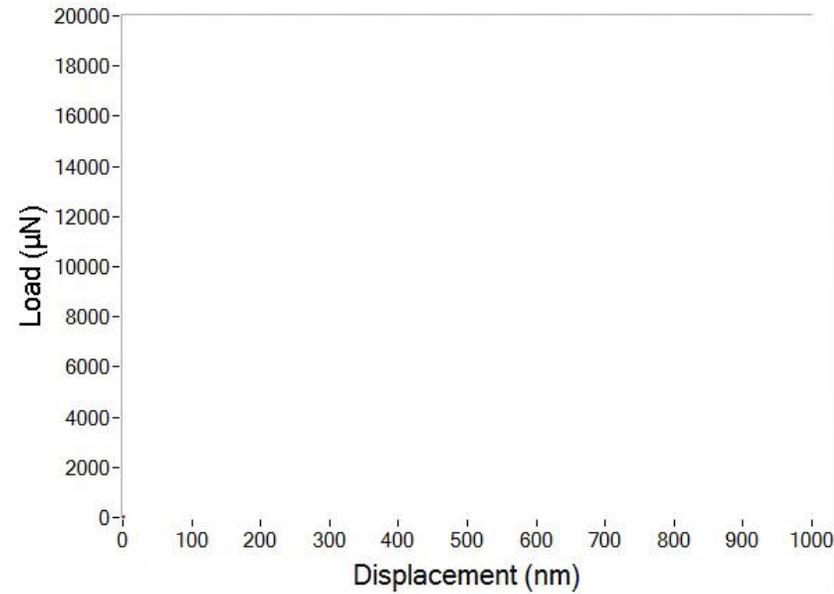


Indentation-Induced Cohesion and Adhesion on Hard Coating

In-situ Nano-Indentation in SEM

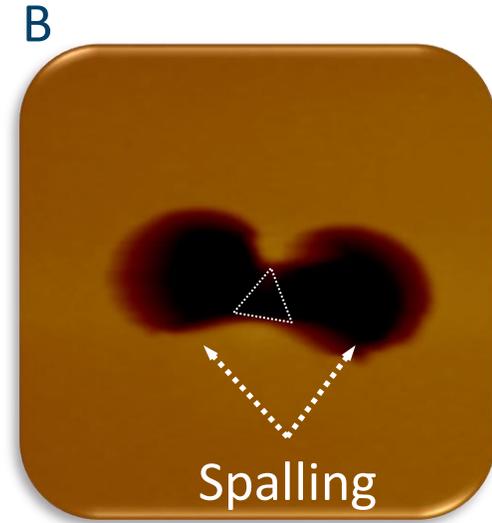
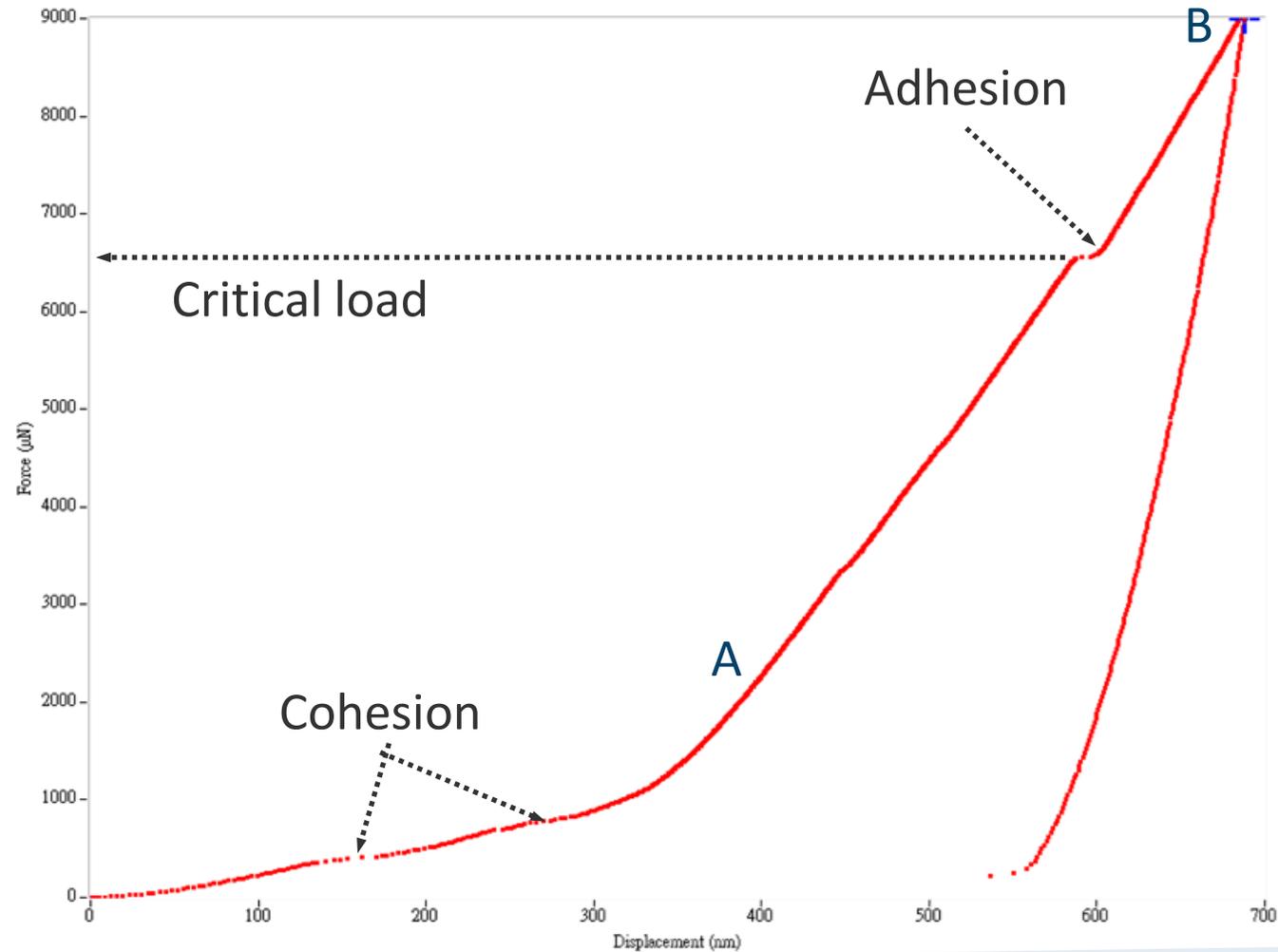
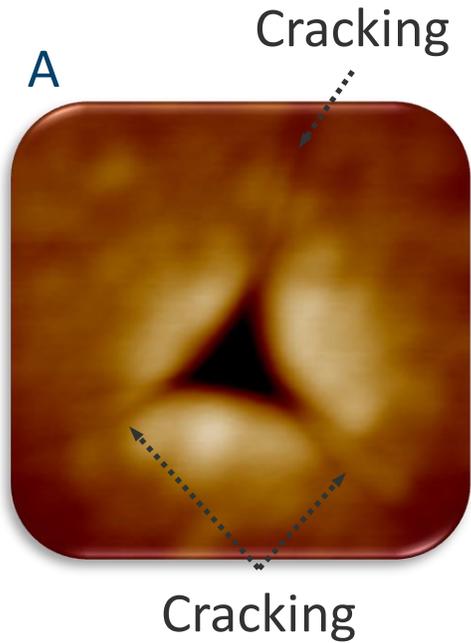


Hysitron PI 89 Picoindenter

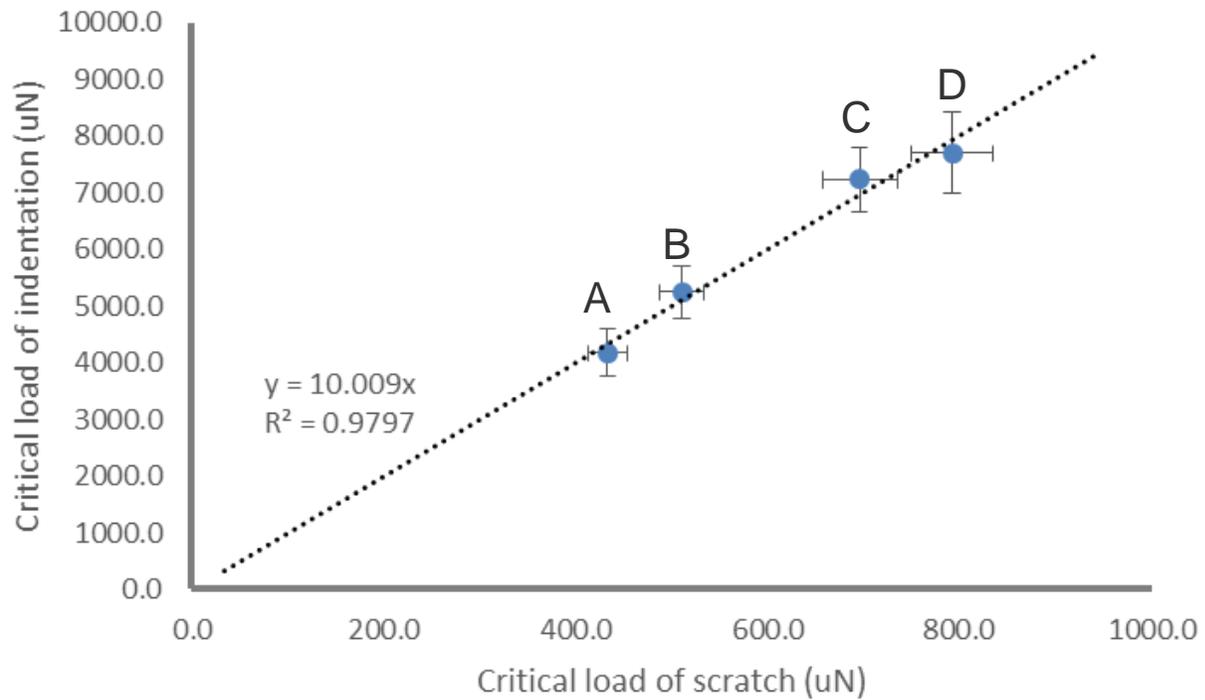
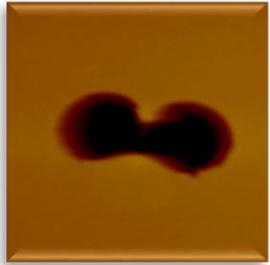


Indentation-Induced Cohesion and Adhesion

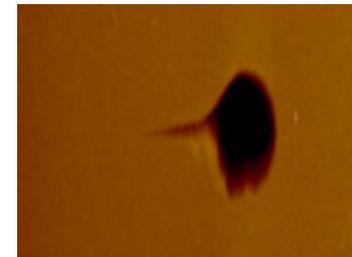
Check of Post- SPM Imaging



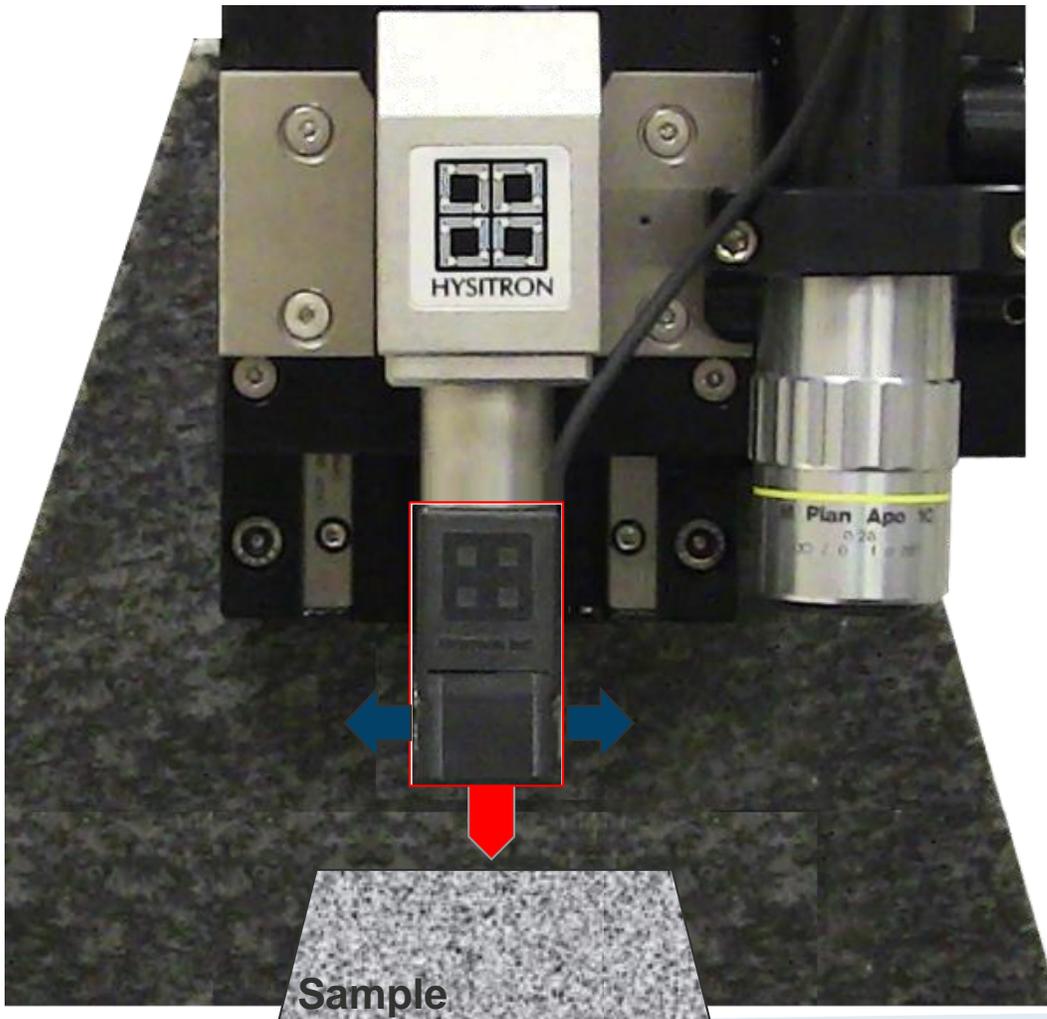
Correlation of Critical Load Results



| Sample | Scratch Method | | Indentation Method | |
|--------|----------------|----------|--------------------|----------|
| | Ave (uN) | Std (uN) | Ave (uN) | Std (uN) |
| C | 696.2 | 38.7 | 7231.2 | 573.5 |
| D | 792.5 | 42.2 | 7702.0 | 715.7 |
| A | 433.3 | 19.9 | 4173.5 | 419.4 |
| B | 510.7 | 22.9 | 5249.3 | 464.3 |



High Speed Indentation with Pop-in Signal



How it works:

- Approach routine makes contact with the sample
- Electrostatic actuation to perform experiment and withdraw
- Between indents, piezo is moved to next position

TI-980: up to 6 indents/s

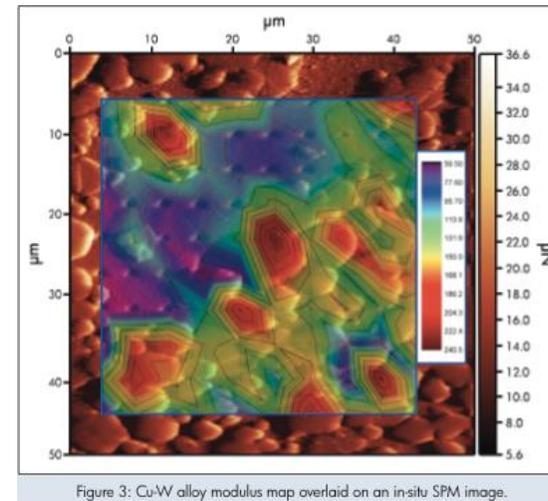
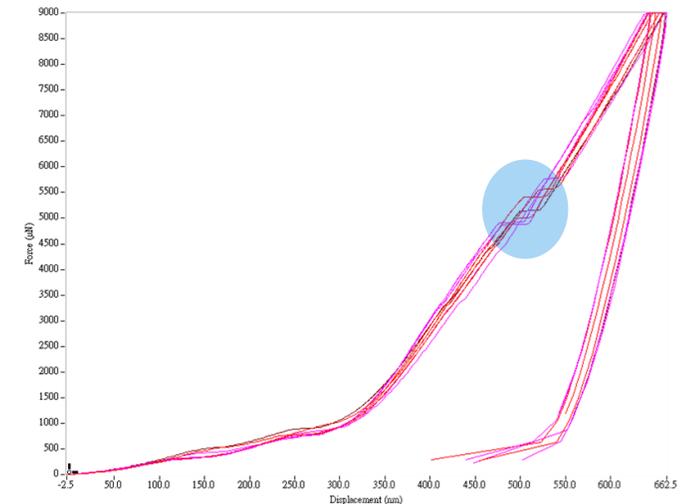
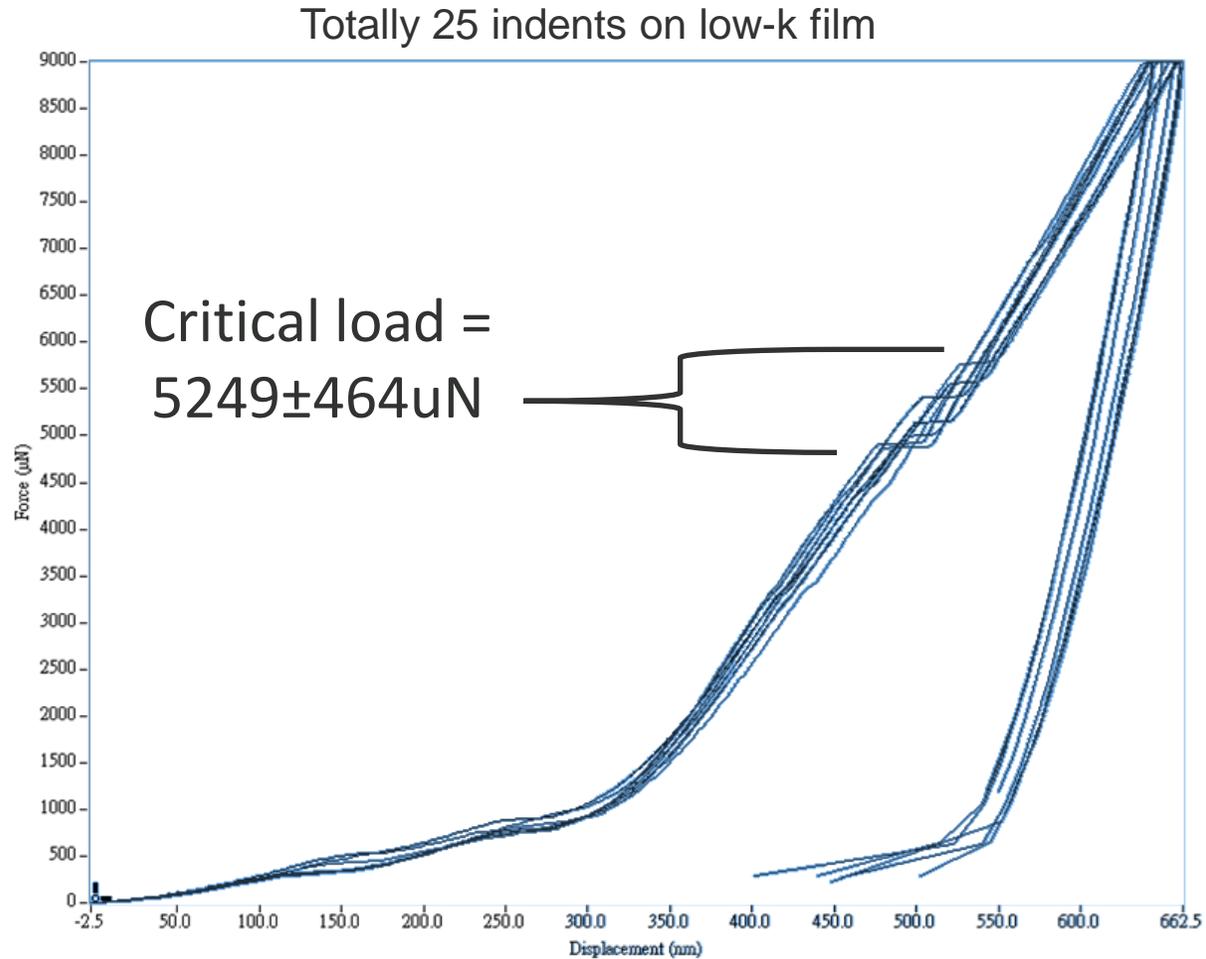


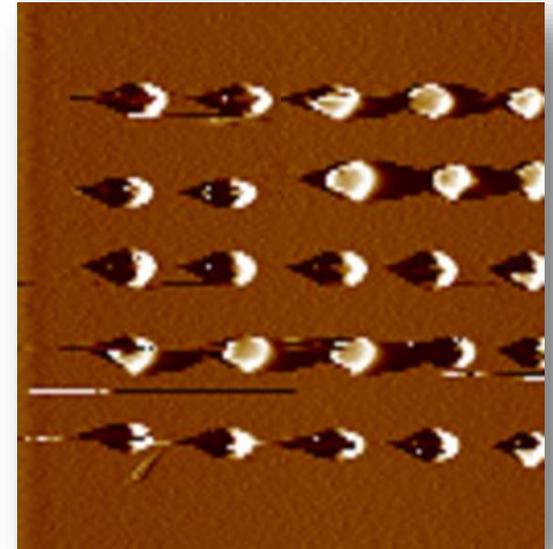
Figure 3: Cu-W alloy modulus map overlaid on an in-situ SPM image.



Indentation-Induced Delamination Using XPM



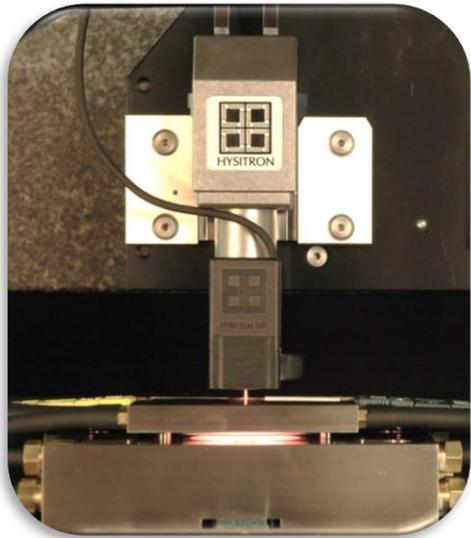
Post-SPM image after XPM



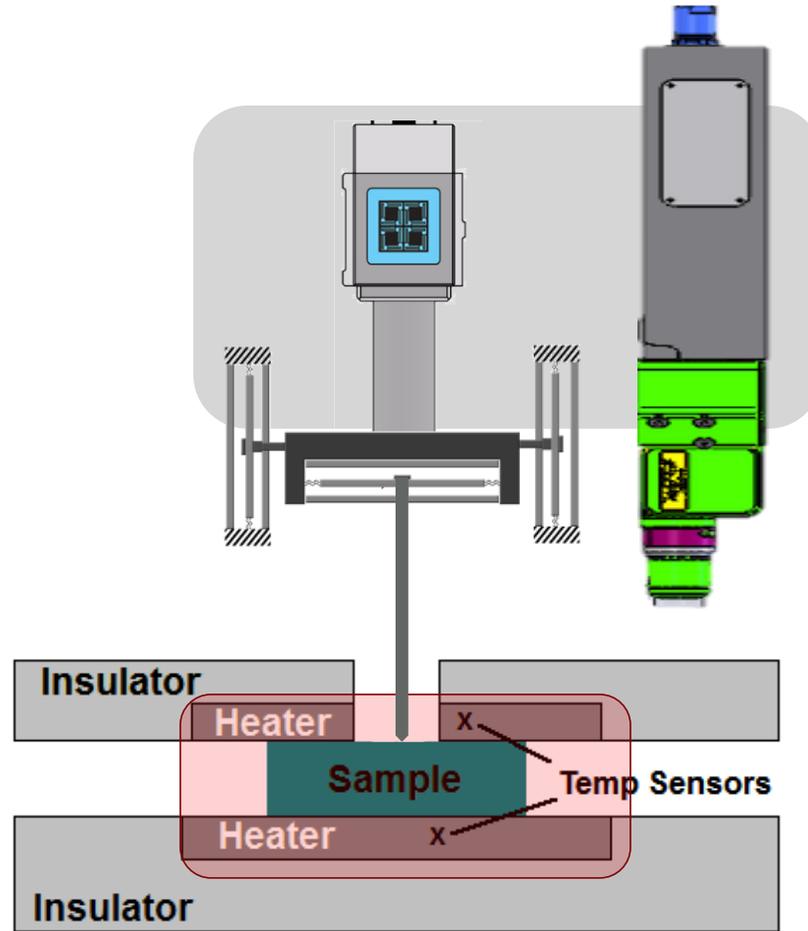
Cube corner tip
Applied load: 9mN
Array: 5x5 @ 30s
Spacing: 15µm

Challenges at Elevated Temperature

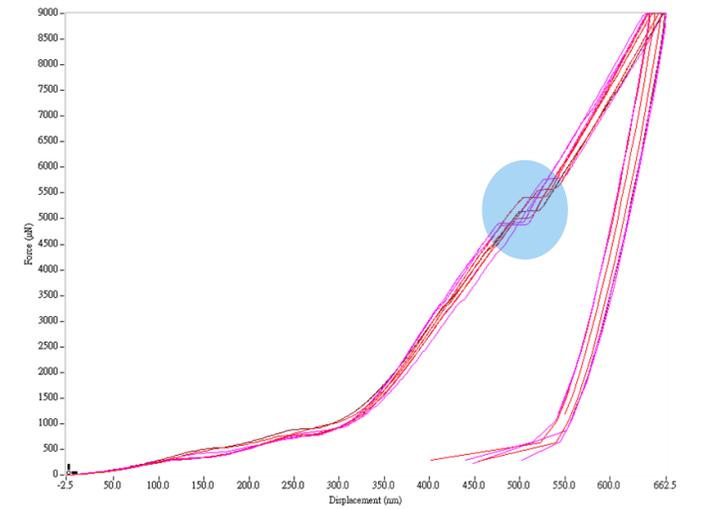
XPM Indentation at Elevated Temperature



xSol heating on TI980



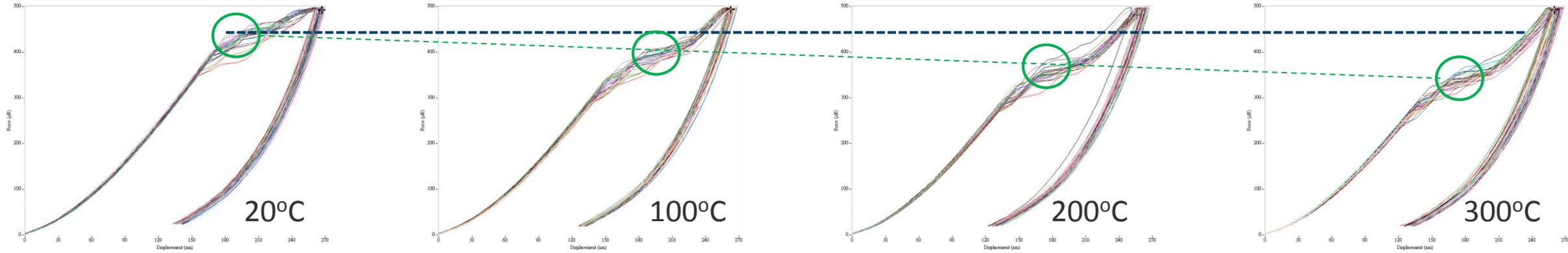
XPM at high temperature



XPM Results at Different Temperature Levels

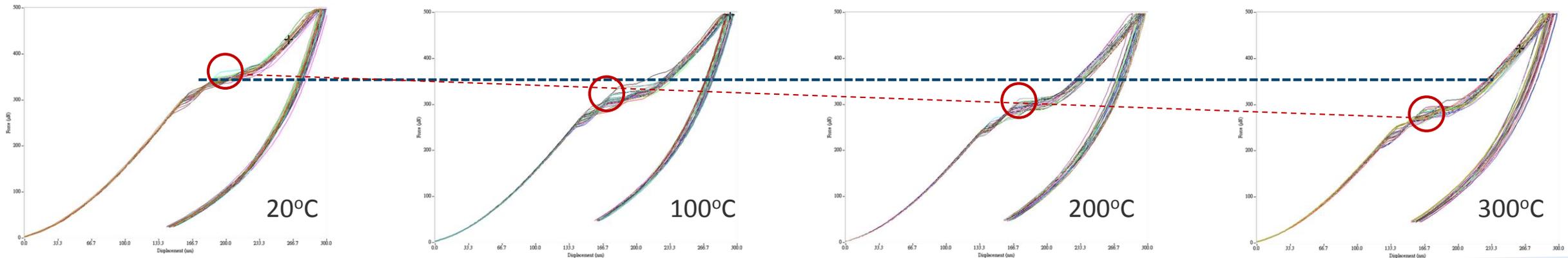
Low-k Films on Silicon

Sample 2



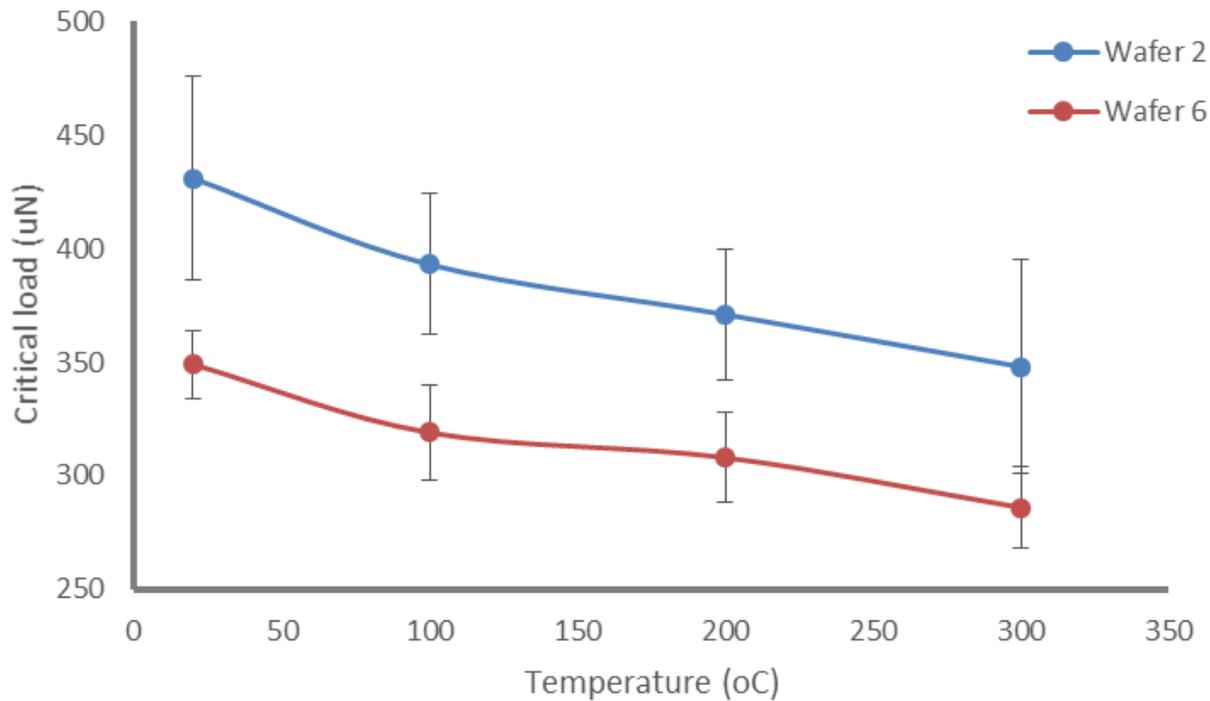
..... : Baseline of critical load at 20°C

Sample 6



Comparison of Critical Load Results at All Temperature Levels

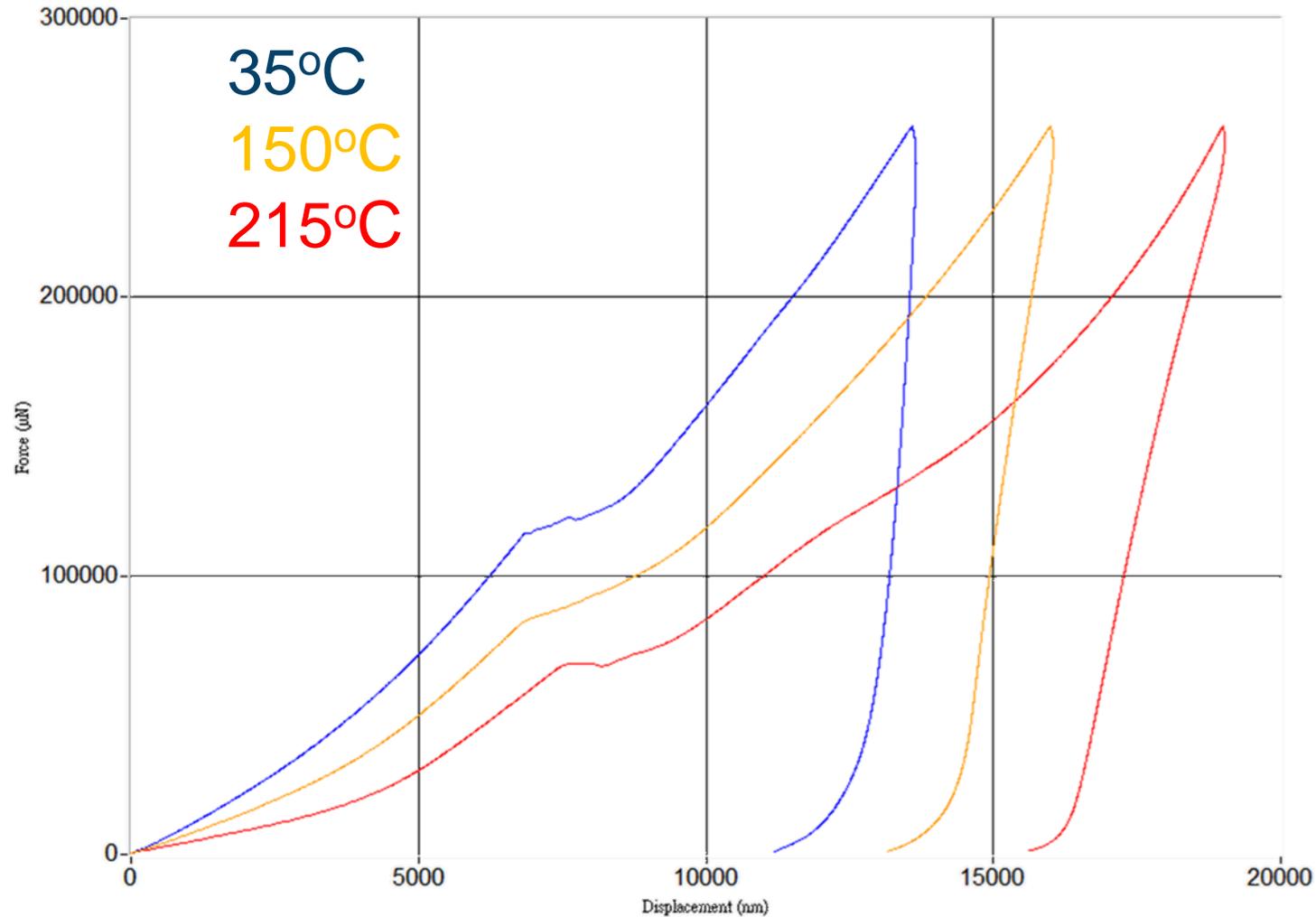
Low-k Films on Silicon



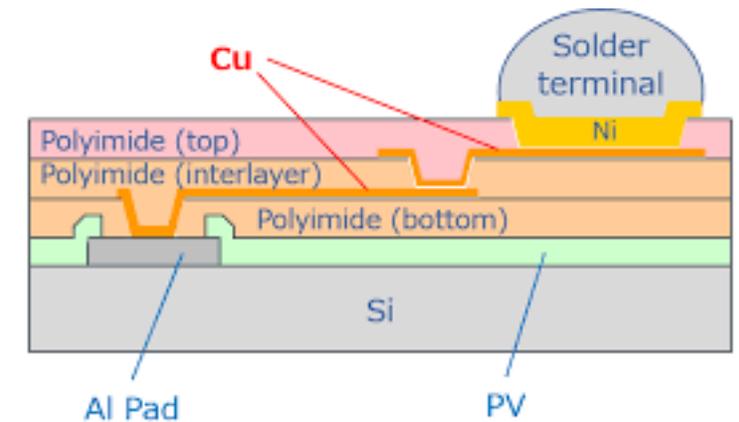
| Wafer 2 | 20°C | 100°C | 200°C | 300°C |
|----------|-------|-------|-------|-------|
| ave (uN) | 431 | 393 | 371 | 348 |
| std (uN) | 45 | 31 | 29 | 47 |
| cv | 10.4% | 7.9% | 7.8% | 13.5% |

| Wafer 6 | 20°C | 100°C | 200°C | 300°C |
|----------|------|-------|-------|-------|
| ave (uN) | 349 | 319 | 308 | 286 |
| std (uN) | 15 | 21 | 20 | 18 |
| cv | 4.3% | 6.6% | 6.5% | 6.3% |

High Load Indentations at Elevated Temperature Polymer Film on Copper



| T (°C) | L _{crit} (uN) | H (GPa) | E (GPa) |
|--------|------------------------|---------|---------|
| 35 | 115218.2 | 0.4963 | 6.02 |
| 150 | 84091.46 | 0.3906 | 4.69 |
| 215 | 68276.05 | 0.1101 | 1.59 |

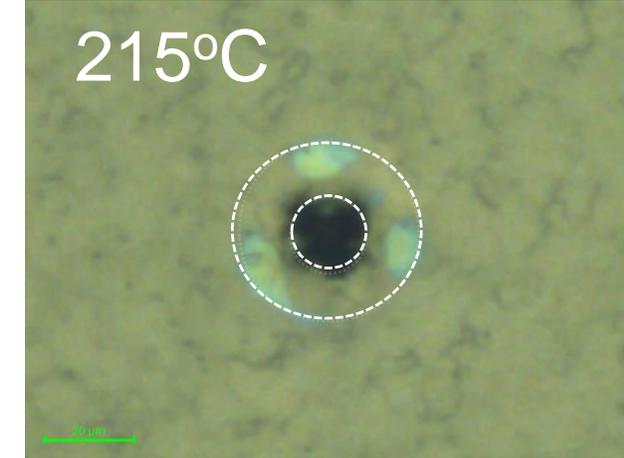
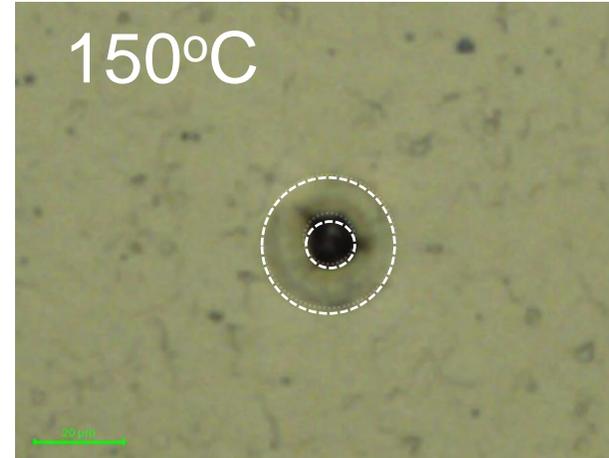
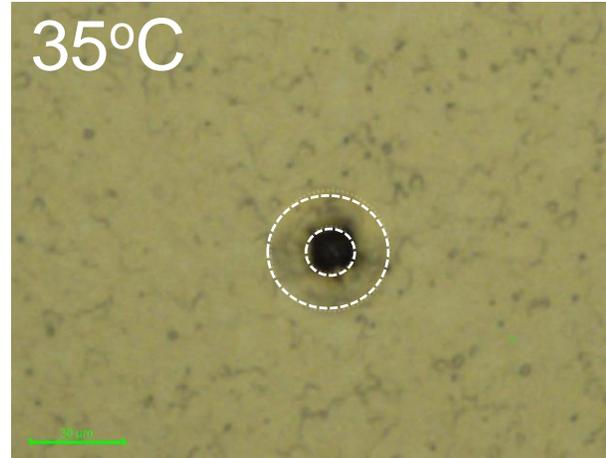
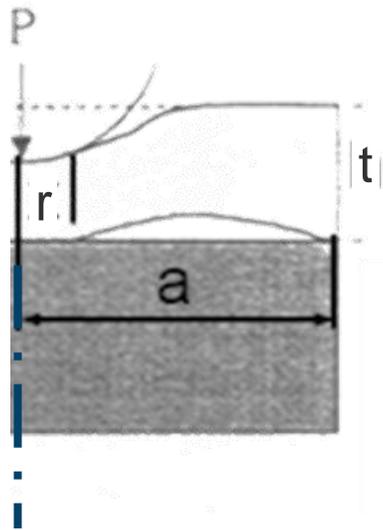


<https://halocarbon.com/more-than-moore-through-advanced-semiconductor-packaging/>

Adhesion Work Calculation at Temperature Levels

Polymer Film on Copper

Post Optical image



$$G = \frac{0.627 \cdot H^2 \cdot t \cdot (1 - \nu^2)}{E} \cdot \left(\frac{1}{1 + \nu + (a/r) \cdot (1 - \nu)} \right)^2$$

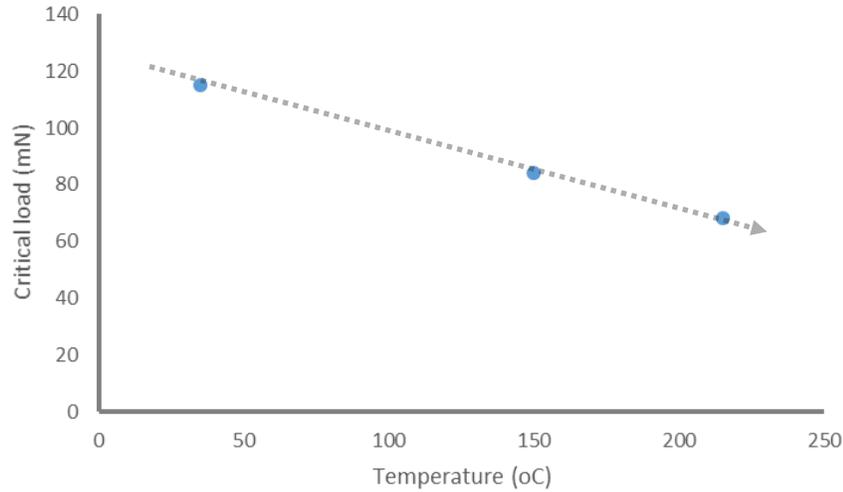
| ν | H (GPa) | T (°C) | E (GPa) | t (nm) | L_{crit} (uN) | a (um) | r (um) | G (J/m ²) |
|-------|---------|--------|---------|--------|-----------------|--------|--------|-----------------------|
| 0.3 | 0.49 | 35 | 6.02 | 10000 | 115218.2 | 30.3 | 11.5 | 6.81 |
| 0.3 | 0.39 | 150 | 4.69 | 10000 | 84091.5 | 40.7 | 16.0 | 6.04 |
| 0.3 | 0.11 | 215 | 1.59 | 10000 | 68276.1 | 41.9 | 17.4 | 1.68 |

L.G. Rosenfeld, et al., *Journal of Applied Physics* **1990**, 67(7), 3291

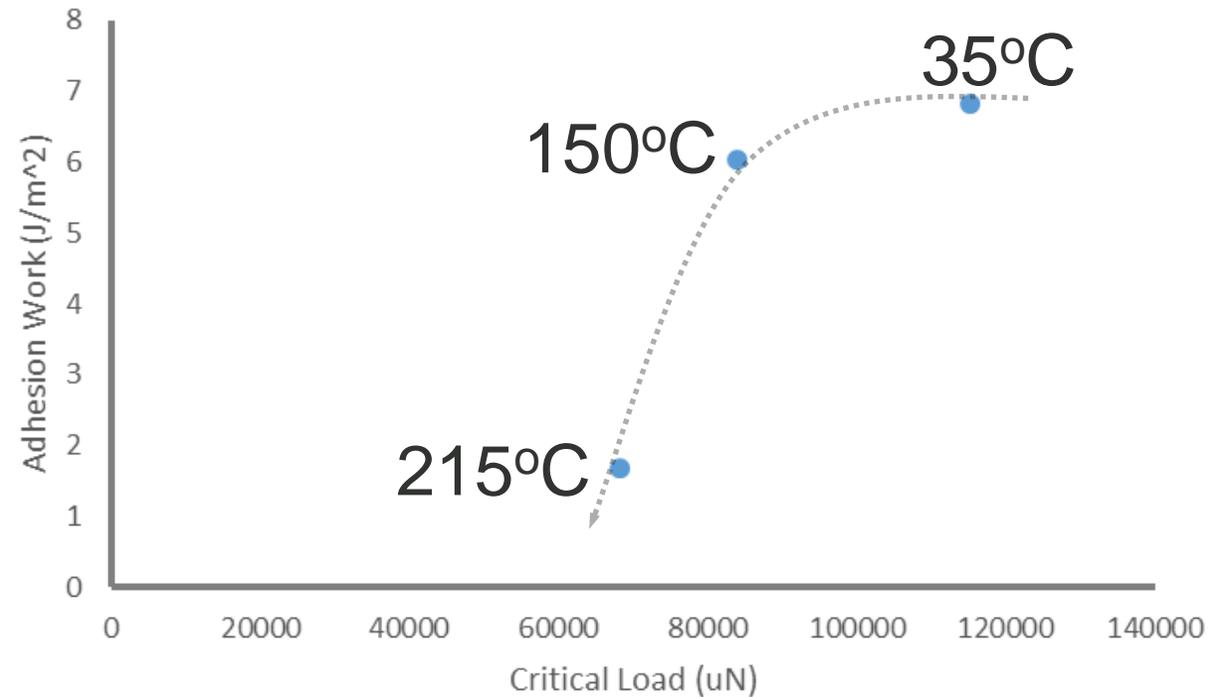
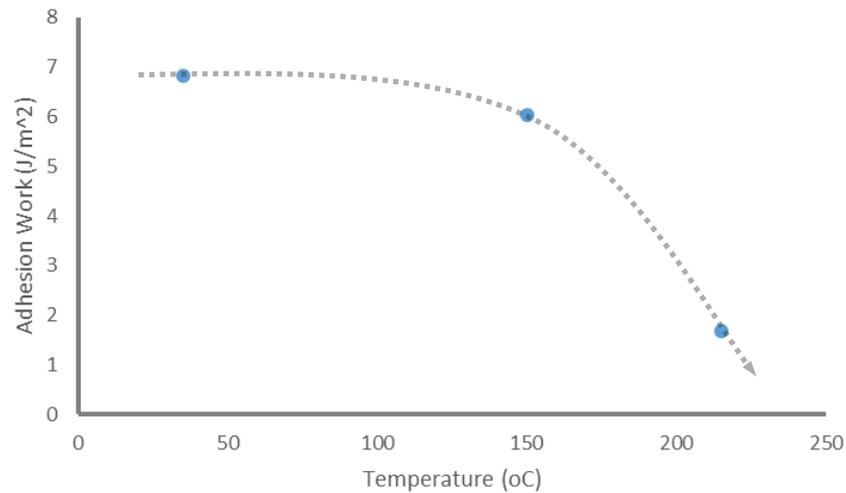
Poisson ratio is assumed to be 0.3 at all temperature levels.

Adhesion Work Calculation at Temperature Levels

Polymer Film on Copper



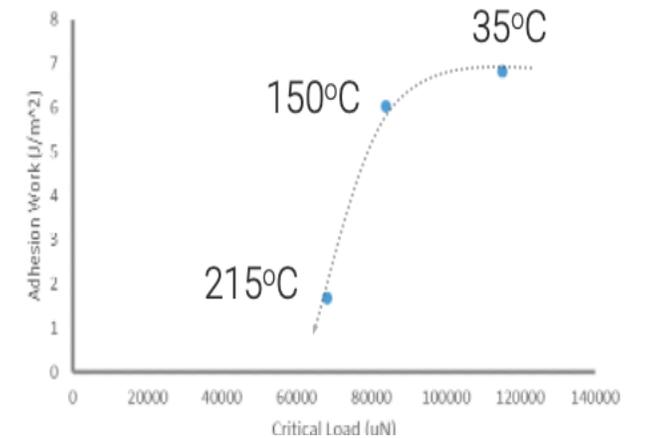
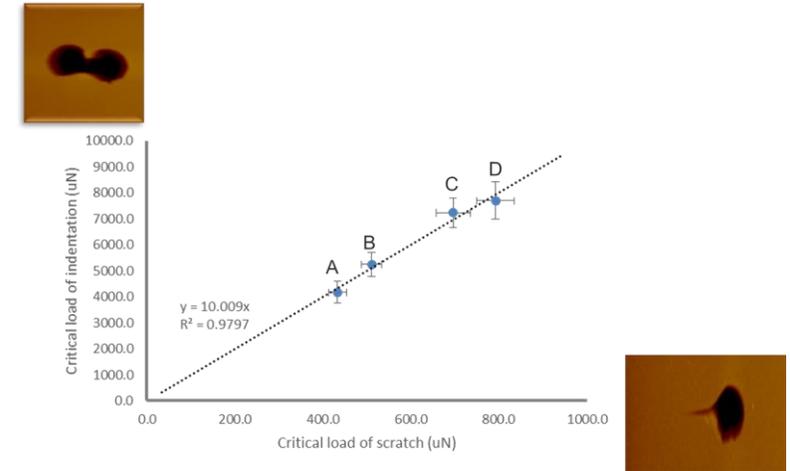
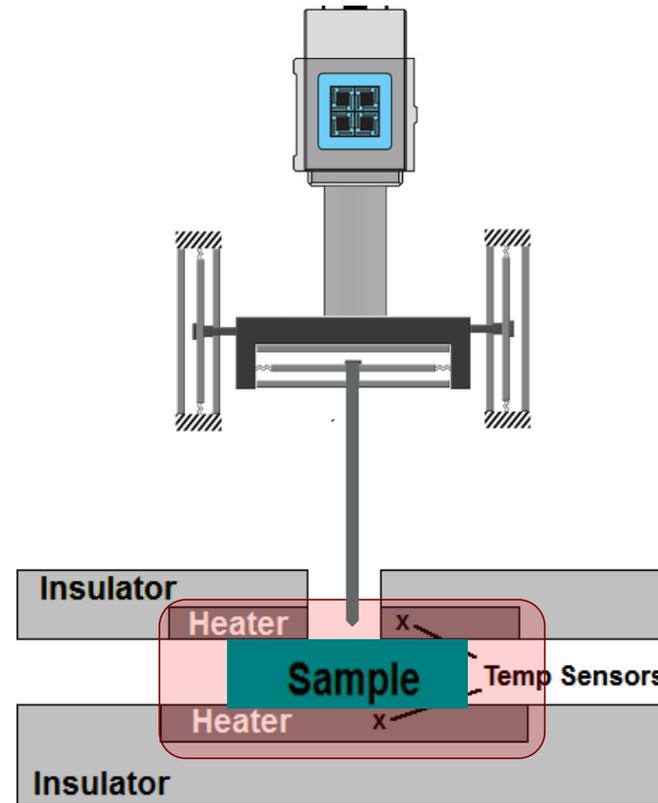
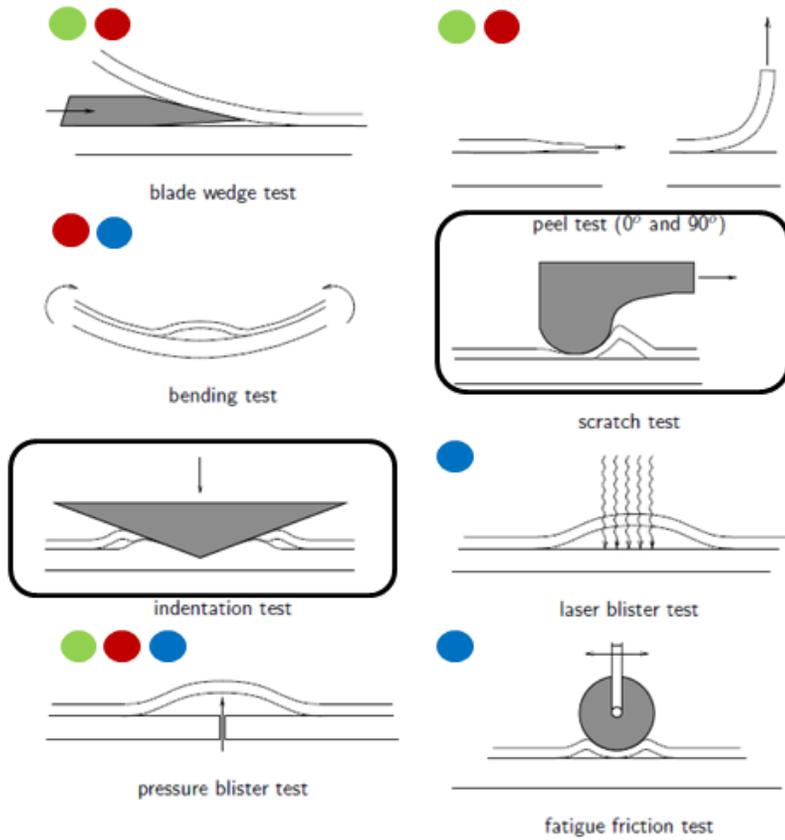
| H (GPa) | T (°C) | E (GPa) | Lcrit (uN) | G (J/m ²) |
|---------|--------|---------|------------|-----------------------|
| 0.49 | 35 | 6.02 | 115218.2 | 6.81 |
| 0.39 | 150 | 4.69 | 84091.5 | 6.04 |
| 0.11 | 215 | 1.59 | 68276.1 | 1.68 |



Take Away

Take Away

- special sample preparation
- Low spatial resolution
- Ex-situ measurement





Thank you!

PJ Wei

Pal-Jen.Wei@bruker.com